

L Number	Hits	Search Text	DB	Time stamp
-	756	(257/288).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/07 17:45
-	2	5191402.URPN.	USPAT	2002/08/08 07:07
-	14	("4301518" "4494301" "4532534" "4654680" "4663645" "4807002" "4808544" "4823172" "4845544" "4855801" "4862233" "4881107" "4907046" "5075762").PN.	USPAT	2002/08/08 07:12
-	196	gate adj electrode same (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:43
-	100	(gate adj electrode same (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.) and gate adj (insulat\$3 dielectric oxide) with thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:19
-	17	((257/288).CCLS.) and (electrode same (Re RH Ir Pt Ru))	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:18
-	95	((gate adj electrode same (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.) and gate adj (insulat\$3 dielectric oxide) with thickness) not (((257/288).CCLS.) and (electrode same (Re RH Ir Pt Ru)))	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:18
-	99	gate adj electrode with (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:42
-	47	((gate adj electrode with (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.) and gate adj (insulat\$3 dielectric oxide) with thickness) not (((257/288).CCLS.) and (electrode same (Re RH Ir Pt Ru)))	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:20
-	46	gate adj electrode with (Re RH Ir Pt Ru) and MOSFET and Si and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:42
-	25	(gate adj electrode with (Re RH Ir Pt Ru) and MOSFET and Si and 257/\$.ccls.) not (((gate adj electrode with (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls.) and gate adj (insulat\$3 dielectric oxide) with thickness) not (((257/288).CCLS.) and (electrode same (Re RH Ir Pt Ru))))	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 07:43
-	0	("l28 and MOSFET").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:06
-	124	(257/388).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:07
-	806	(257/412).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:07
-	0	("l30 and MOSFET").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:08
-	168	((257/412).CCLS.) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2002/08/08 08:08

-	49	gate adj electrode same (Re Rhenium) and MOSFET and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/08 08:45
-	20	gate adj electrode with (Re Rhenium) and MOSFET and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/08 08:45
-	51	gate adj electrode with (Re RH Ir Pt Ru) and oxide and Si and 257/\$.ccls. and gate adj (insulat\$3 dielectric oxide) with thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/08 10:11